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ON Semiconductor™

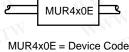
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ULTRAFAST RECTIFIER 4.0 AMPERES 800-1000 VOLTS





MARKING DIAGRAM



MUR4x0E = Device Code x = 8 or 10

ORDERING INFORMATION

Device	Package	Shipping
MUR480E	Axial Lead	5000 Units/Bag
MUR480ERL	Axial Lead	1500/Tape & Reel
MUR4100E	Axial Lead	5000 Units/Bag
MUR4100ERL	Axial Lead	1500/Tape & Reel

SWITCHMODE™ Power Rectifiers

Ultrafast "E" Series with High Reverse Energy Capability

... designed for use in switching power supplies, inverters and as free wheeling diodes, these state-of-the-art devices have the following features:

- 20 mJ Avalanche Energy Guaranteed
- Excellent Protection Against Voltage Transients in Switching Inductive Load Circuits
- Ultrafast 75 Nanosecond Recovery Time
- 175°C Operating Junction Temperature
- Low Forward Voltage
- Low Leakage Current
- High Temperature Glass Passivated Junction
- Reverse Voltage to 1000 Volts

Mechanical Characteristics:

- Case: Epoxy, Molded
- Weight: 1.1 gram (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 220°C Max. for 10 Seconds, 1/16" from case
- Shipped in plastic bags, 5,000 per bag
- Available Tape and Reeled, 1500 per reel, by adding a "RL" suffix to the part number
- Polarity: Cathode indicated by Polarity Band
- Marking: MUR480E, MUR4100E

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage MUR480E MUR4100E	V _{RRM} V _{RWM} V _R	800 1000	WW
Average Rectified Forward Current (Square Wave) (Mounting Method #3 Per Note 2.)	I _{F(AV)}	4.0 @ T _A = 35°C	Α
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I _{FSM}	70 OM TW	А
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-65 to +175	°C

THERMAL CHARACTERISTICS

THERMAL CHARACTERISTICS					
Maximum Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	See Note 2.	°C/W		

Characteristic	Symbol	Max
Maximum Instantaneous Forward Voltage (Note 1.) $ (i_F = 3.0 \text{ Amps}, T_J = 150^{\circ}\text{C}) $ $ (i_F = 3.0 \text{ Amps}, T_J = 25^{\circ}\text{C}) $ $ (i_F = 4.0 \text{ Amps}, T_J = 25^{\circ}\text{C}) $	WWW.1 VFOM	1.53 1.75 1.85
Maximum Instantaneous Reverse Current (Note 1.) (Rated dc Voltage, $T_J = 100^{\circ}\text{C}$) (Rated dc Voltage, $T_J = 25^{\circ}\text{C}$)	WWW V.10 PR. CO	900 25
Maximum Reverse Recovery Time $ (I_F = 1.0 \text{ Amp, di/dt} = 50 \text{ Amp/}\mu\text{s}) $ $ (I_F = 0.5 \text{ Amp, } I_R = 1.0 \text{ Amp, } I_{REC} = 0.25 \text{ Amp}) $	t _{rr}	100 75
Maximum Forward Recovery Time (I _F = 1.0 Amp, di/dt = 100 Amp/μs, Recovery to 1.0 V)	t _{fr}	75
Controlled Avalanche Energy (See Test Circuit in Figure 6.)	W _{AVAL}	20

^{1.} Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%. WWW.100Y.CO

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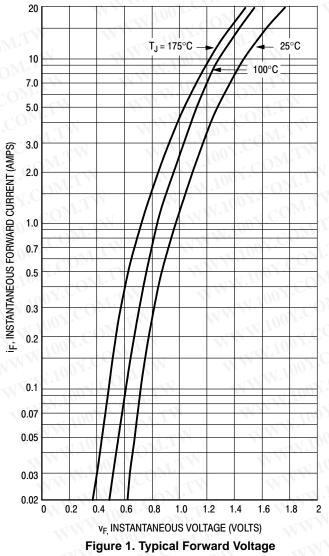
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MUR480E, MUR4100E

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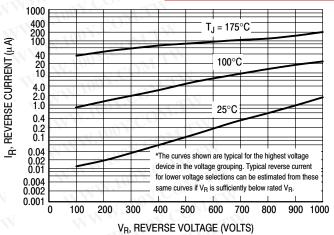


Figure 2. Typical Reverse Current*

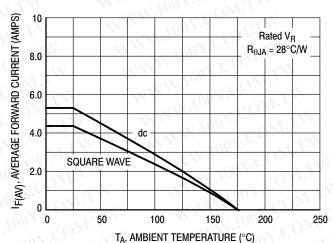


Figure 3. Current Derating (Mounting Method #3 Per Note 1)

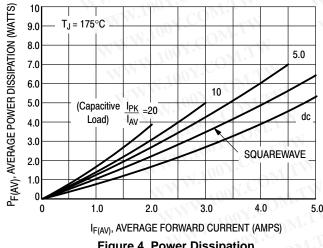


Figure 4. Power Dissipation

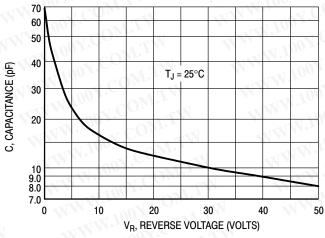


Figure 5. Typical Capacitance

D V_D

Figure 6. Test Circuit

BV_{DUT}

I_L

V_{DD}

t₀

t₁

t₂

t

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Figure 7. Current-Voltage Waveforms

The unclamped inductive switching circuit shown in Figure 6. was used to demonstrate the controlled avalanche capability of the new "E" series Ultrafast rectifiers. A mercury switch was used instead of an electronic switch to simulate a noisy environment when the switch was being opened.

When S_1 is closed at t_0 the current in the inductor I_L ramps up linearly; and energy is stored in the coil. At t_1 the switch is opened and the voltage across the diode under test begins to rise rapidly, due to di/dt effects, when this induced voltage reaches the breakdown voltage of the diode, it is clamped at BV_{DUT} and the diode begins to conduct the full load current which now starts to decay linearly through the diode, and goes to zero at t_2 .

By solving the loop equation at the point in time when S_1 is opened; and calculating the energy that is transferred to the diode it can be shown that the total energy transferred is equal to the energy stored in the inductor plus a finite amount of energy from the V_{DD} power supply while the diode is in breakdown (from t_1 to t_2) minus any losses due to finite

component resistances. Assuming the component resistive elements are small Equation (1) approximates the total energy transferred to the diode. It can be seen from this equation that if the V_{DD} voltage is low compared to the breakdown voltage of the device, the amount of energy contributed by the supply during breakdown is small and the total energy can be assumed to be nearly equal to the energy stored in the coil during the time when S_1 was closed, Equation (2).

The oscilloscope picture in Figure 8., shows the information obtained for the MUR8100E (similar die construction as the MUR4100E Series) in this test circuit conducting a peak current of one ampere at a breakdown voltage of 1300 volts, and using Equation (2) the energy absorbed by the MUR8100E is approximately 20 mjoules.

Although it is not recommended to design for this condition, the new "E" series provides added protection against those unforeseen transient viruses that can produce unexplained random failures in unfriendly environments.

EQUATION (1):

MERCURY

$$W_{AVAL} \approx \frac{1}{2}LI_{LPK}^{2} \left(\frac{BV_{DUT}}{BV_{DUT}^{-V}DD} \right)$$

EQUATION (2):

$$W_{AVAL} \approx \frac{1}{2}LI_{LPK}^2$$

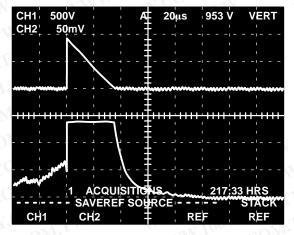


Figure 8. Current-Voltage Waveforms

CHANNEL 2: I_L 0.5 AMPS/DIV

CHANNEL 1: V_{DUT} 500 VOLTS/DIV

TIME BASE: 20 μs/DIV.

NOTE 2. – AMBIENT MOUNTING DATA

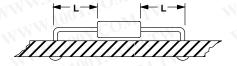
Data shown for thermal resistance junction—to—ambient $(R_{\theta JA})$ for the mountings shown is to be used as typical guideline values for preliminary engineering or in case the tie point temperature cannot be measured.

TYPICAL VALUES FOR $R_{\theta JA}$ IN STILL AIR

Mounting		Lead Length, L (IN)			-1 CC	
Met	Method		1/4	1/2	3/4	Units
1	$C_{\Omega_{M_{\bullet}}}$	50	51	53	55	°C/W
2	$R_{\theta JA}$	58	59	61	63	°C/W
3	1.00	TW	2	28	. 41	°C/W

MOUNTING METHOD 1

P.C. Board Where Available Copper Surface area is small.

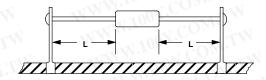


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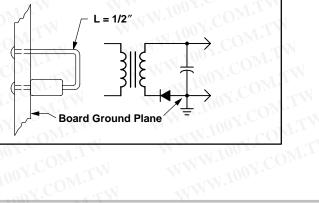
MOUNTING METHOD 2

Vector Push-In Terminals T-28



MOUNTING METHOD 3

P.C. Board with 1–1/2" x 1–1/2" Copper Surface



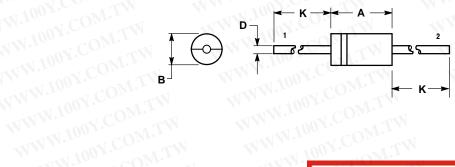
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W.100Y.COM.TW NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.

. 00	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.287	0.374	7.30	9.50	
В	0.189	0.209	4.80	5.30	
D	0.047	0.051	1.20	1.30	
K	1.000		25.40	J. 272	

STYLE 1:

PIN 1. CATHODE (POLARITY BAND)

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